

IR2167

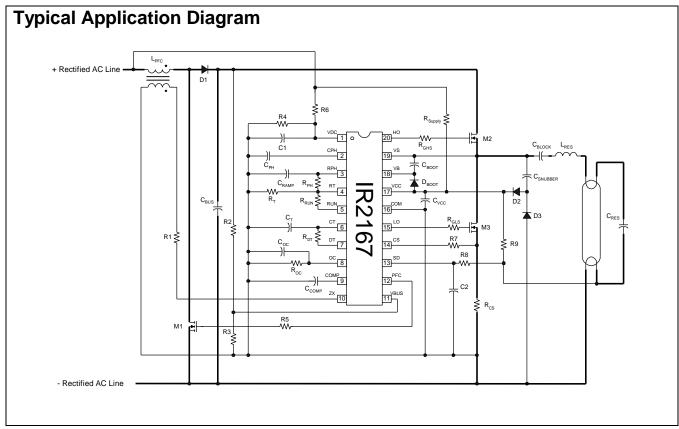
PFC BALLAST CONTROL IC

Description

The IR2167 is a fully integrated, fully protected 600V ballast control IC designed to drive virtually all types of rapid start fluorescent lamp ballasts. PFC circuitry provides for high PF, low THD and DC Bus regulation. Externally programmable features such as preheat time & frequency, ignition ramp characteristics, and running mode operating frequency provide a high degree of the ballast flexibility for design engineer. Comprehensive protection features such as protection from failure of a lamp to strike, filament failures, low AC line conditions, thermal overload, or lamp failure during normal operation, as well as an automatic restart function, have been included in the design. The heart of this control IC is a variable frequency oscillator with externally programmmable deadtime. Precise control of a 50% duty cycle is accomplished using a T-flip-flop. The IR2167 is available in both 20 pin DIP and 20 pin wide body SOIC packages.

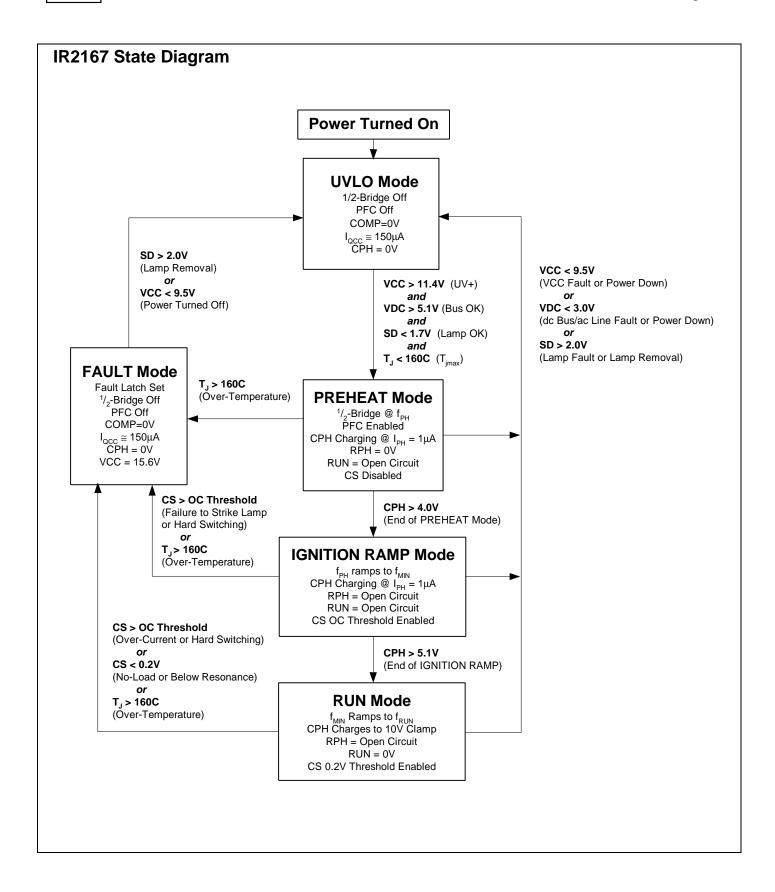
Features

- PFC, Ballast Control and Half Bridge Driver in One IC
- Critical Conduction Mode Boost Type PFC
- No PFC Current Sense Resistor Required
- Programmable Preheat Time & Frequency
- Programmable Ignition Ramp
- Programmable Over-Current
- Lamp Filament Sensing & Protection
- Capacitive Mode Protection
- Brown-Out Protection
- Automatic Restart for Lamp Exchange
- Thermal Overload Protection
- Programmable Deadtime
- Internal 15.6V Zener Clamp Diode on Vcc
- Micropower Startup (150µA)
- Latch Immunity and ESD Protection

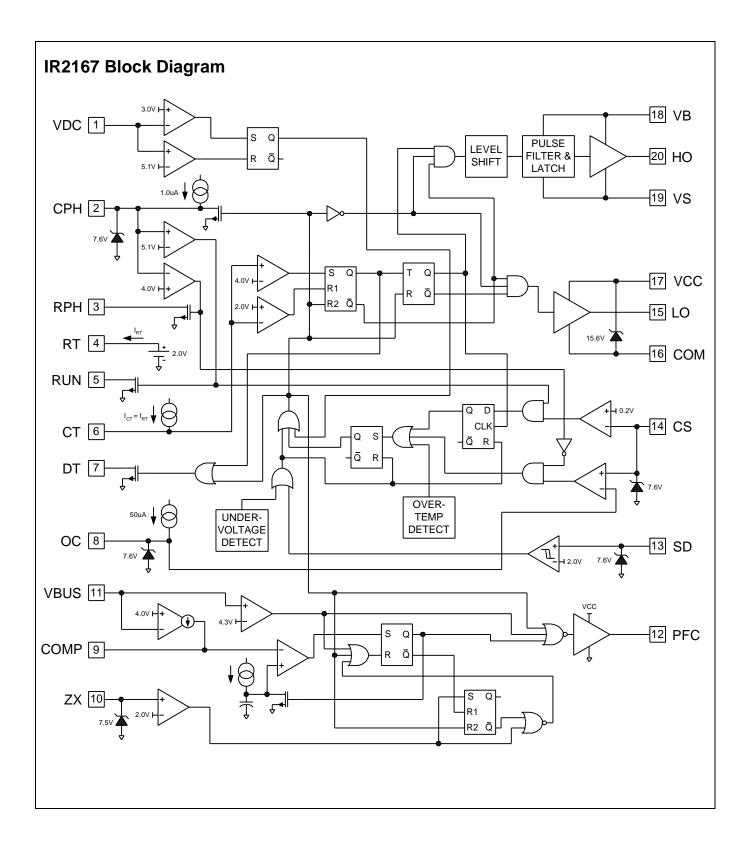


* Please note that this datasheet contains advanced information which could change before the product is released to production.

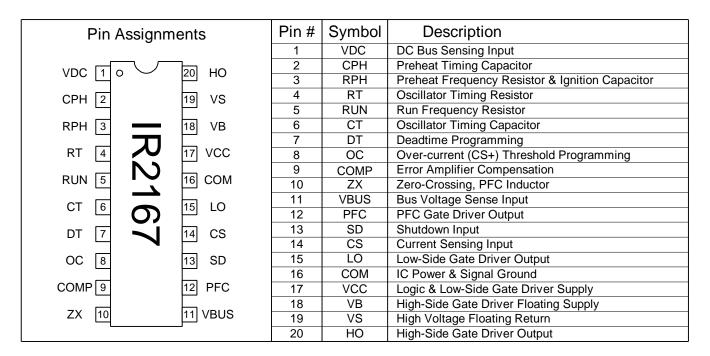












Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

	Parameter			
Symbol	Definition	Min.	Max.	Units
V _B	High Side Floating Supply Voltage	-0.3	625	V
Vs	High Side Floating Supply Offset Voltage	V _B - 25	$V_B + 0.3$	V
V_{HO}	High-Side Floating Output Voltage	V _S - 0.3	V _B + 0.3	V
V _{LO}	Low-Side Output Voltage	-0.3	V _{CC} + 0.3	V
VPFC	PFC Gate Driver Output Voltage	-0.3	Vcc + 0.3	V
I _{OMAX}	Maximum Allowable Output Current (HO, LO, PFC) Due to External Power Transistor Miller Effect	-500	500	mA
I _{RT}	R _T Pin Current	-5	5	mA
V _{CT}	Ст Pin Voltage	-0.3	6.5	V
V_{DC}	VDC Pin Voltage	-0.3	V _{cc} + 0.3	V
I _{CPH}	CPH Pin Current	-5	5	mA
I _{RPH}	RPH Pin Current	-5	5	mA
I _{RUN}	RUN Pin Current	-5	5	mA
I _{DT}	Deadtime Pin Current	-5	5	mA
Vcs	Current Sense Pin Voltage	-0.3	6.5	V
I _{CS}	Current Sense Pin Current	-5	5	mA
loc	Over-Current Threshold Pin Current	-5	5	mA
I _{SD}	Shutdown Pin Current	-5	5	mA
VBUS	DC Bus Sensing Input Voltage	-0.3	Vcc	V
Izx	PFC Inductor Current, Zero Crossing Detection Input	-5	5	mA



Absolute Maximum Ratings (Continued)

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

	Parameter			
Symbol	Definition	Min.	Max.	Units
Ісомр	PFC Error Amplifier Compensation Current	-5	5	mΑ
Icc	Supply Current (Note 1)	-20	20	mΑ
dV/dt	Allowable Offset Voltage Slew Rate	-50	50	V/ns
P _D	Package Power Dissipation @ T _A ≤ +25°C (20-Pin DIP)		1.50	W
P _D	Package Power Dissipation @ T _A ≤ +25°C (20-Pin SOIC)		1.25	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (20-Pin		85	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (20-Pin		90	°C/W
TJ	Junction Temperature	-55	150	
Ts	Storage Temperature	-55	150	۰C
TL	Lead Temperature (Soldering, 10 seconds)		300	

Note 1: This IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Please note that the Vcc pin should not be driven by a DC, low impedance voltage source greater than the V_{CLAMP} specified in the Electrical Characteristics section.

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead.

	Parameter			
Symbol	Definition	Min.	Max.	Units
V_{BS}	High Side Floating Supply Voltage	V _{CC} - 0.7	V _{CLAMP}	V
Vs	Steady State High Side Floating Supply Offset Voltage	-3.0	600	V
Vcc	Supply Voltage	V _{CCUV+}	V_{CLAMP}	V
Icc	Supply Current	Note 2	10	mA
V_{DC}	VDC Pin Voltage	0	Vcc	V
Ст	CT Pin Capacitance	220		pF
R _{DT}	Deadtime Resistance	1.0		kΩ
I _{RT}	R _T Pin Current (Note 3)	-500	-50	μΑ
I _{RPH}	RPH Pin Current (Note 3)	0	450	μΑ
I _{RUN}	RUN Pin Current (Note 3)	0	450	μΑ
I _{SD}	Shutdown Pin Current	-1	1	mA
I _{CS}	Current Sense Pin Current	-1	1	mA
I _{ZX}	Zero Crossing Detection Pin Current	-1	1	mA
TJ	Junction Temperature	-40	125	۰C

Note 2: Sufficient current should be supplied to the VCC pin to keep the internal 15.6V zener clamp diode on this pin regulating its voltage.

Note 3: Due to the fact that the RT pin is a voltage-controlled current source, the total RT pin current is the sum of all of the parallel current sources connected to that pin. For optimum oscillator current mirror performance, this total current should be kept between 50μA and 500μA. During the preheat mode, the total current flowing out of the RT pin consists of the RPH pin current plus the current due to the RT resistor. During the run mode, the total RT pin current consists of the RUN pin current plus the the current due to the RT resistor.



Electrical Characteristics

 $V_{CC}=V_{BS}=V_{BIAS}=14V~+/-~0.25V,~R_T=40.0~k\Omega,~C_T=470~pF,~RPH~and~RUN~pins~no~connection,~V_{CPH}=0.0~V,~R_{DT}=6.1~k\Omega,~R_{OC}=20.0~k\Omega,~V_{CS}=0.5~V,~V_{SD}=0.0~V,~C_L=1000pF~unless~otherwise~specified.$

Parameter		T	$T_A = 25^{\circ}C$			
Symbol	Definition	Min	Тур	Max	Units	Test Conditions
Supply	Characteristics	1		I.		
V _{CCUV} +	V _{CC} Supply Undervoltage Positive Going Threshold		11.4			V _{CC} rising from 0V
V _{UVHYS}	V _{CC} Supply Undervoltage Lockout Hysteresis		1.8			
Iqccuv	UVLO Mode Quiescent Current		150		μΑ	Vcc < Vccuv-
IQCCFLT	Fault-Mode Quiescent Current		200		μA	$SD = 5V$, $CS = 2V$, or $Tj > T_{SD}$
Iqcc	Quiescent VCC Supply Current		3.8		mA	RT no connection, CT connected to
I _{QCC50k}	VCC Supply Current, f = 50kHz		4.5		mA	R_T =36K ohm, R_{DT} = 5.6K ohm, C_T =220pF
V_{CLAMP}	V _{CC} Zener Clamp Voltage		15.6		V	$I_{CC} = 10mA$
Floating	Supply Characteristics					
I _{QBS0}	Quiescent V _{BS} Supply Current		0			$V_{HO} = V_{S}$
I _{QBS1}	Quiescent V _{BS} Supply Current		30		μA	$V_{HO} = V_{B}$
V _{BSMIN}	Minimum required V _{BS} Voltage for proper HO functionality		4	5	V	
I _{LK}	Offset Supply Leakage Current			50	μA	V _B = V _S = 600V
PFC Err	or Amplifier Characteristics					
V_{VBUS}	VBUS Sense Input Threshold		4.0		V	
I _{VBUS}	VBUS Sense Input Bias Current			0.1	μA	
gm	Error Amplifier Transconductance		100		μmho	
Isource	Error Amplifier Output Current Sourcing		60		μA	VvBus = 3.2V
I _{SINK}	Error Amplifier Output Current Sinking		60		μA	Vvbus = 4.8V
V _{OH(EA)}	Error Amplifier Output Voltage Swing (High State)		10		V	Vvbus = 3.2V
$V_{\text{OL(EA)}}$	Error Amplifier Output Voltage Swing (Low State)		1		V	VvBUS = 4.8V
PFC Ove	ervoltage Comparator					
Vov	Overvoltage Comparator Threshold		4.3		V	
PFC Zer	o Current Detector					
Vzx	ZX Pin Comparator Threshold Voltage		2.0		V	
Vzxhys	ZX Pin Comparator Hysterisis		120		mV	
VzXclamp+	ZX Pin Clamp Voltage (High State)		7.5		V	Izx = 2mA



Electrical Characteristics (Continued)

 $V_{CC} = V_{BS} = V_{BIAS} = 14V + /-0.25V, R_T = 40.0 \ k\Omega, C_T = 470 \ pF, RPH \ and RUN \ pins \ no \ connection, V_{CPH} = 0.0 \ V, R_{DT} = 6.1 \ k\Omega, R_{OC} = 20.0 \ k\Omega, V_{CS} = 0.5 \ V, V_{SD} = 0.0 \ V, C_L = 1000 pF \ unless \ otherwise \ specified.$

Parameter T		A = 25°C				
Symbol	Definition	Min	Тур	Max	Units	Test Conditions
Oscillat	or, Ballast Control, I/O Characteristics			I		
fosc	Oscillator Frequency		30			$R_T = 32 \text{ k}\Omega, R_{DT} =$
					kHz	6.1kΩ, Cτ = 470 pF
			100			$R_T = 6.1 \text{ k}\Omega, R_{DT} = 6.1 \text{k}\Omega, C_T = 470 \text{ pF}$
df/dV	Oscillator Frequency Voltage Stability		0.5		%/V	V _{CCUV+} < VCC < 15V
df/dT	Oscillator Frequency Temperature Stability		0.02		%/C	-40°C < Tj < 125°C
d	Oscillator Duty Cycle		50		%	
V _{CT+}	Upper C _T Ramp Voltage Threshold		4.0		V	
V _{CT} -	Lower C _T Ramp Voltage Threshold		2.0		, v	
V _{CTFLT}	Fault-Mode C _T Pin Voltage		0		mV	SD = 5V, CS = 2V, or
						Tj > T _{SD}
V_{RT}	RT Pin Voltage		2.0		V	
V_{RTFLT}	Fault-Mode R _T Pin Voltage		0		mV	SD = 5V, CS = 2V, or
						Tj > T _{SD}
tdlo	LO Output Deadtime		2.0		µsec	
tdho	HO Output Deadtime		2.0		µsec	
dtd/dV	Deadtime Voltage Stability		0.5		%/V	V _{CCUV+} < V _{CC} < 15V
dtd/dT	Deadtime Temperature Stability		0.02		%/C	-40°C < Tj < 125°C
Preheat	Characteristics					
I _{CPH}	CPH Pin Charging Current		1.0		μΑ	VCPH = 0V
V _{CPHIGN}	CPH Pin Ignition Mode Threshold Voltage		4.0			
V _{CPHRUN}	CPH Pin Run Mode Threshold Voltage		5.15		V	
V _{CPHCLM}	CPH Pin Clamp Voltage		10			Ісрн = 1µА
V_{CPHFLT}	Fault-Mode CPH Pin Voltage		0		mV	SD = 5V, CS = 2V, or
DDU Ob						$T_i > T_{SD}$
1	aracteristics			ı		
I _{RPHLK}	Open Circuit RPH Pin Leakage Current		0.1		μA	VRPH = 5V, VPH = 6V
V _{RPHFLT}	Fault-Mode RPH Pin Voltage		0		mV	SD = 5V, $CS = 2V$, or
RUN Ch	aracteristics		<u> </u>		<u> </u>	$T_i > T_{SD}$
I _{RUNLK}	Open Circuit RUN Pin Leakage Current		0.1		μA	V _{RUN} =5V
V_{RUNFLT}	Fault-Mode RUN Pin Voltage		0		mV	SD = 5V, CS = 2V, or
						Ti > Tsn



Electrical Characteristics (Continued)

 $V_{CC} = V_{BS} = V_{BIAS} = 14V$ +/- 0.25V, $R_T = 40.0$ k Ω , $C_T = 470$ pF, RPH and RUN pins no connection, $V_{CPH} = 0.0$ V, $R_{DT} = 6.1$ k Ω , $R_{OC} = 20.0$ k Ω , $V_{CS} = 0.5$ V, $V_{SD} = 0.0$ V, $C_L = 1000$ pF unless otherwise specified.

Parameter		$T_A = 25^{\circ}C$				
Symbol	Definition	Min	Тур	Max	Units	Test Conditions
Protectio	n Circuitry Characteristics					
V _{SDTH+}	Rising Shutdown Pin Threshold Voltage		2.0		V	
V _{SDHYS}	Shutdown Pin Threshold Hysteresis		150		mV	
V _{CSTH₊}	Over-Current Sense Threshold Voltage		1.0		V	
V _{CSTH} -	Under-Current Sense Threshold Voltage		0.2		V	
t _{cs}	Over-Current Sense Propogation Delay		160		nsec	Delay from CS to LO
V _{DC+}	Low V _{BUS} /Rectified Line Input Upper Threshold		5.15		V	
V_{DC}	Low V _{BUS} /Rectified Line Input Lower Threshold		3.0		V	
T _{SD}	Thermal Shutdown Junction Temperature		160		°C	Note 4
Gate Driv	er Output Characteristics					
VoL	Low-Level Output Voltage		0	100	mV	I _O = 0
V _{OH}	High-Level Output Voltage		0	100	''''	$V_{BIAS} - V_{O}$, $I_{O} = 0$
t _r	Turn-On Rise Time		85	150	nsec	
t _f	Turn-Off Fall Time		45	100		

Note 4: When the IC senses an overtemperature condition ($T_j > 160^{\circ}$ C), the IC is latched off. In order to reset this Fault Latch, the SD pin must be cycled high and then low, or the VCC supply to the IC must be cycled below the falling undervoltage lockout threshold (Vccuv-).

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